

Vishay Siliconix

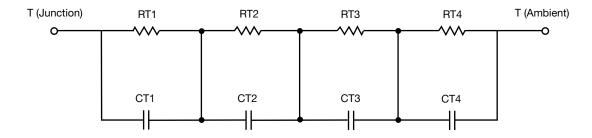
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RT1	N/A	549.6307m	N/A			
RT2	N/A	1.8358	N/A			
RT3	N/A	1.2538	N/A			
RT4	N/A	265.3410m	N/A			
	THERMAL CAPAC	ITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	N/A	386.8237u	N/A			
CT2	N/A	32.1334m	N/A			
CT3	N/A	2.4395m	N/A			
CT4	N/A	1.6610	N/A			

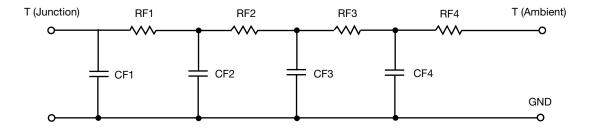
Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	N/A	979.5767m	N/A		
RF2	N/A	1.4211	N/A		
RF3	N/A	463.2464m	N/A		
RF4	N/A	1.0192	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	404.5950u	N/A		
CF2	N/A	4.4401m	N/A		
CF3	N/A	47.7255m	N/A		
CF4	N/A	14.8160m	N/A		

Note

• n/a indicates not applicable





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